

Supporting Information

Fabrication of Pores in a Silicon Carbide Wafer by Electrochemical Etching with a Glassy-Carbon Needle Electrode

*Tomohiko Sugita, Kazuki Hiramatsu, Shigeru Ikeda and Michio Matsumura**

Research Center for Solar Energy Chemistry, Osaka University, 1-3 Machikaneyama, Toyonaka, Osaka
560-8531, Japan

*CORRESPONDING AUTHOR E-mail: matsu@chem.es.osaka-u.ac.jp

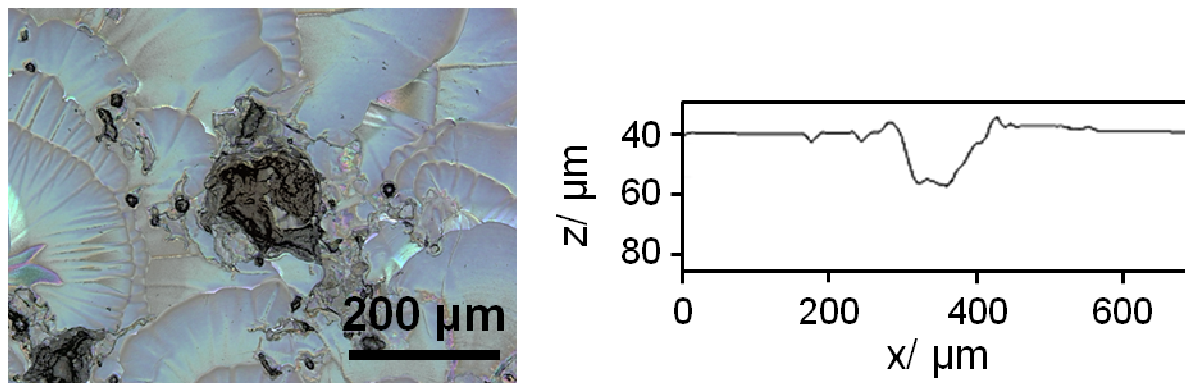


Figure S1. Plan-view micrograph and the depth profile of a pore formed in SiC by electrochemical processing for 5 h with a GC electrode in 20 mol dm^{-3} HF solution containing K_2SO_4 at a concentration of 3 mol dm^{-3} . The potential applied to the GC electrode was 10 V vs Ag/AgCl. Depth profile of the pore is shown along a line passing through the center of the pore.